NXPLQSC20650W

Silicon Carbide Diode

Rev.02 - 07 November 2019

Product data sheet

1. General description

Dual Silicon Carbide Schottky diode in a 3-lead TO247 plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
 - Telecom / Server SMPS
- UPS
- PV inverter
- Electrical Vehicle Charger
- Motor Drives

4. Quick reference data

| able 1. Q | uick reference data | | | | | | 1 |
|--------------------|---------------------------------|--|-------------|----|------|------|----|
| Symbol | Parameter | Conditions | Values | | | Unit | |
| Absolute | maximum rating | | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | | 6 | 50 | | V |
| I _{O(AV)} | average forward current | δ = 0.5 ; square-wave pulse; T _{mb} ≤ 74 °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3 | | 20 | | A | |
| Tj | junction temperature | | 175 | | °C | | |
| Symbol | Parameter | Conditions | Min Typ Max | | Unit | | |
| Static ch | aracteristics | | | | | | |
| V _F | forward voltage | $I_F = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 5$ | | - | 1.65 | 1.85 | V |
| | | I _F = 10 A; T _j = 150 °C; per diode; <u>Fig. 5</u> | | - | 2.1 | 2.5 | V |
| Dynamic | characteristics | ·, | | | , | | |
| Q _r | recovered charge | $I_{F} = 10 \text{ A}; \text{ d}_{F}/\text{d}t = 500 \text{ A}/\mu\text{s}; \text{ V}_{R} = 400 \text{ V};$ T_{j} = 25 °C; per diode; <u>Fig. 7</u> | | - | 12 | - | nC |



5. Pinning information

| Table 2. P | inning infor | mation | | |
|------------|--------------|-------------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | A1 | anode | | |
| 2 | К | cathode | | |
| 3 | A2 | anode | | <u> </u> |
| mb | mb | mounting base; connected to cathode | | sym125 |

6. Ordering information

| Table 3. Ordering information | | | | | | | | |
|-------------------------------|-----------------|-----------------------|-------------------|---------------------------|-----------------|-----------------------|--|--|
| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date | | |
| NXPLQSC20650W | TO247 | NXPLQSC20650W6Q | Tube | 30 | TO247N | 20-July-2016 | | |

7. Marking

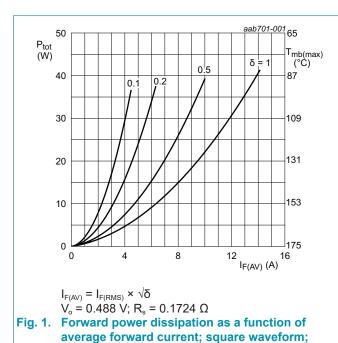
| Table 4. Marking codes | | | | | |
|------------------------|-------------------|--|--|--|--|
| Type number | Marking codes | | | | |
| NXPLQSC20650W | NXPLQSC 20650W | | | | |

8. Limiting values

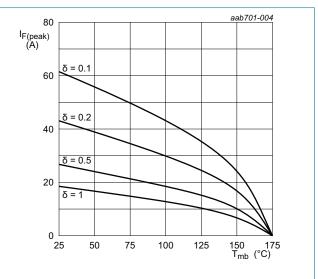
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Values | Unit |
|--------------------|--|---|------------|------------------|
| V _{RRM} | repetitive peak reverse voltage | | 650 | V |
| V _{RWM} | crest working reverse voltage | | 650 | V |
| V _R | reverse voltage | DC | 650 | V |
| I _{O(AV)} | average forward current | δ = 0.5; square-wave pulse; T _{mb} ≤ 74 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> | 20 | A |
| I _{FRM} | repetitive peak forward current | δ = 0.5; t _p = 25 µs; T _{mb} ≤ 88 °C; square-wave pulse; per diode | 20 | A |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode | 48 | A |
| | | t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode | 385 | A |
| l ² t | I ² t for fusing | sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms | 11.5 | A ² s |
| T _{stg} | storage temperature | | -55 to 175 | °C |
| Tj | junction temperature | | 175 | °C |

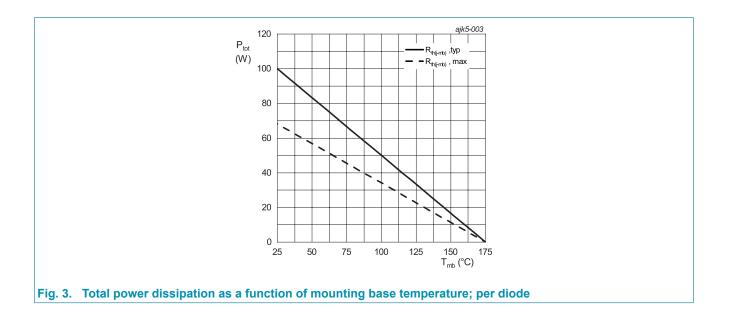


maximum values; per diode



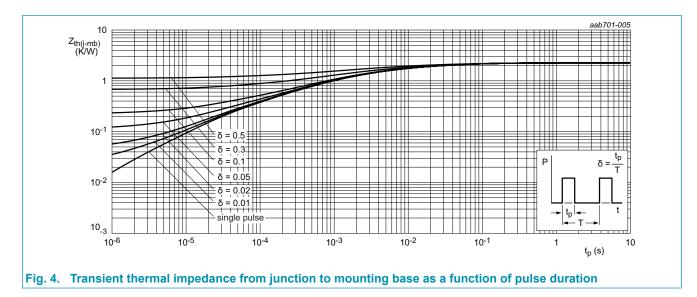


NXPLQSC20650W Silicon Carbide Diode



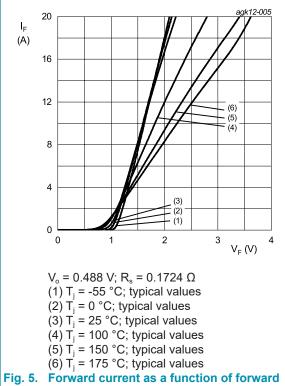
9. Thermal characteristics

| Table 6. Th | ermal characteristics | | | | | |
|-----------------------|--|--------------------------|-----|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
| $R_{\text{th(j-mb)}}$ | thermal resistance from junction to mounting base | per diode; <u>Fig. 4</u> | - | 1.5 | 2.2 | K/W |
| | | both diodes conducting | | 0.9 | 1.3 | K/W |
| $R_{\text{th(j-a)}}$ | thermal resistance from junction to ambient free air | in free air | - | 45 | - | K/W |



10. Characteristics

| Table 7. C | haracteristics | | | | | _ |
|-----------------|------------------------------------|--|-----|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| V _F | forward current | $I_F = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 5$ | - | 1.65 | 1.85 | V |
| | | $I_F = 10 \text{ A}; T_j = 150 \text{ °C}; \text{ per diode}; Fig. 5$ | - | 2.1 | 2.5 | V |
| I _R | reverse current | V_{R} = 650 V; T _j = 25 °C; per diode; <u>Fig. 6</u> | - | - | 50 | μA |
| | | V_{R} = 650 V; T _j = 150 °C; per diode; <u>Fig. 6</u> | - | - | 200 | μA |
| Dynamic | characteristics | · · · · | | | - | |
| Q _r | recovered charge | I _F = 10 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 25 °C; per diode; <u>Fig. 7</u> | - | 12 | - | nC |
| C _d | diode capacitance | f = 1 MHz; V _R = 1 V; T _j = 25 °C | - | 267 | - | pF |
| | | f = 1 MHz; V _R = 300 V; T _j = 25 °C | - | 37 | - | pF |
| | | f = 1 MHz; V _R = 600 V; T _j = 25 °C | - | 36 | - | pF |
| E _{as} | non-repetitive avalanche energy | $I_R = 4.9 \text{ A}; \text{ L} = 5 \text{ mH}; \text{ T}_{j(init)} = 25 \text{ °C};$ per diode | 60 | - | - | mJ |





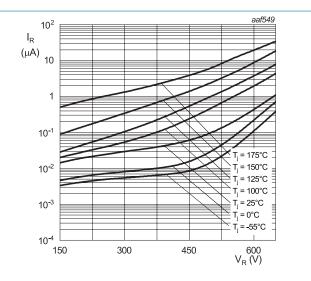
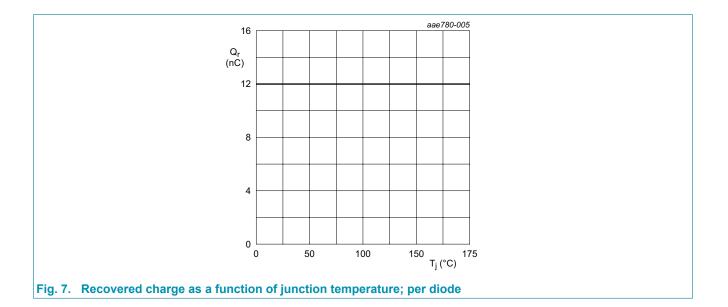


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

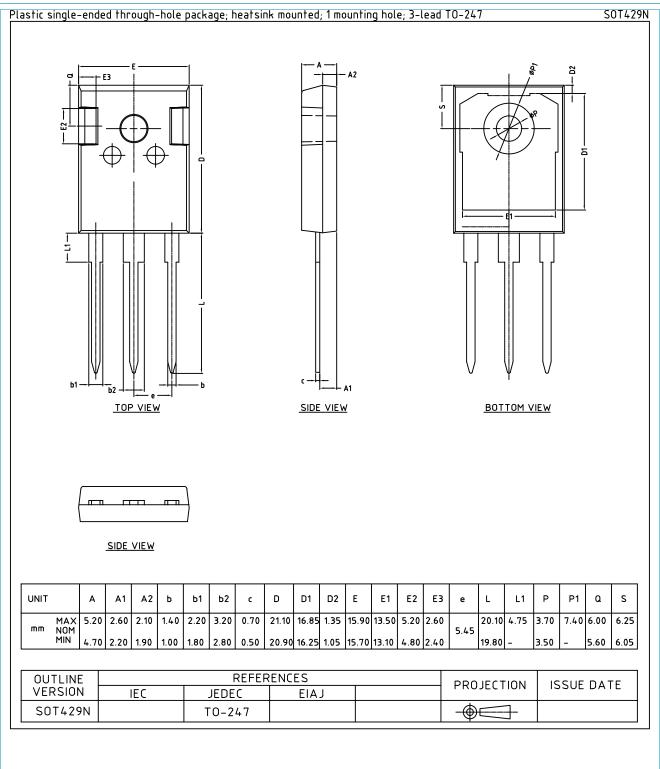
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NXPLQSC20650W

Silicon Carbide Diode



11. Package outline



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Silicon Carbide Diode

12. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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- [2] The term 'short data sheet' is explained in section "Definitions".
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